

Silicon Dioxide Etch STS RIE

Equipment

Procedure

1. Mask Material: AZ1518,AZ9260 photoresist.
2. Etch Recipe:
 1. Power = 100W
 2. SF₆ flow rate = 20sccm
 3. Pressure = 100mT
 4. SiO₂ etch rate = 100 Å/min

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